Octal D-Type Latch with 3-State Output

The MC74VHC373 is an advanced high speed CMOS octal latch with 3–state output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input and an output enable input. When the output enable input is high, the eight outputs are in a high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

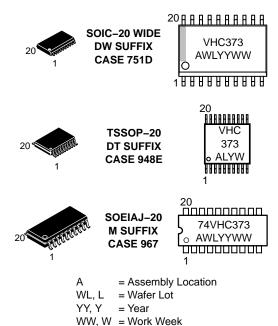
- High Speed: $t_{PD} = 5.0 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4.0 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.9 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 186 FETs or 46.5 Equivalent Gates
- Pb–Free Packages are Available*



ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

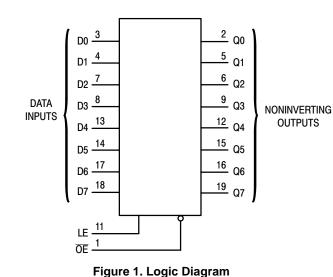


PIN ASSIGNMENT							
OE [1•	20	þ	V _{CC}			
Q0 [2	19	þ	Q7			
D0 [3	18	þ	D7			
D1 [4	17	þ	D6			
Q1 [5	16	þ	Q6			
Q2 [6	15	þ	Q5			
D2 [7	14	þ	D5			
D3 [8	13	þ	D4			
Q3 [9	12	þ	Q4			
GND [10	11	þ	LE			

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



FUNCTION TABLE

	INPUTS	OUTPUT	
ŌĒ	LE	D	q
L L L H	H H L X	H L X X	H L No Change Z

MAXIMUM RATINGS

Symbol	Paramete	Value	Unit	
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
Vout	DC Output Voltage	$-$ 0.5 to V_{CC} + 0.5	V	
Ι _{ΙΚ}	Input Diode Current	- 20	mA	
I _{OK}	Output Diode Current		± 20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V_{CC} and G	ND Pins	± 75	mA
PD	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		– 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature	- 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 3.3 \text{ V} \\ V_{CC} = 5.0 \text{ V}$	0 0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V_{CC} $T_A = 25^{\circ}C$ $T_A = -$		Vec	T _A = 25°C		$T_A = -40$	0 to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit	
V _{IH}	Minimum High–Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V	
VIL	Maximum Low–Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V	
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80			
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μA	
I _{OZ}	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or } GND$	5.5			± 0.25		± 2.5	μΑ	
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			4.0		40.0	μΑ	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

				T _A = 25°C		$T_A = 25^{\circ}C$ $T_A = -40 \text{ to } 85^{\circ}C$		0 to 85°C	2
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, D to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		7.3 9.8	11.4 14.9	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.9 6.4	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, LE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C _L = 15 pF C _L = 50 pF		5.0 6.5	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 15 pF C _L = 50 pF		7.3 9.8	11.4 14.9	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ R _L = 1 kΩ			5.5 7.0	8.1 10.1	1.0 1.0	9.5 11.5	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Q	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C _L = 50 pF		9.5	13.2	1.0	15.0	ns
		$V_{CC} = 5.0 \pm 0.5 V$ R _L = 1 k Ω	C _L = 50 pF		6.5	9.2	1.0	10.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 V$ (Note 1)	C _L = 50 pF			1.5		1.5	ns
		$V_{CC} = 5.5 \pm 0.5 V$ (Note 1)	C _L = 50 pF			1.0		1.0	ns

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

			T _A = 25°C		$T_A = -40$ to $85^{\circ}C$			
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
C _{in}	Maximum Input Capacitance			4	10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State)			6				pF
				Tvr	nical @ 25	°C. Vec =	50V	

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 2)	27	pF

Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per latch). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter	Тур	Мах	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.6	- 0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

TIMING REQUIREMENTS (Input $t_r = t_f = 3.0 \text{ ns}$)

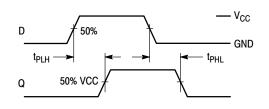
			T _A =	: 25°C	T _A = − 40 to 85°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Unit
t _{w(h)}	Minimum Pulse Width, LE	$V_{CC} = 3.3 \pm 0.3 V$ $V_{CC} = 5.0 \pm 0.5 V$		5.0 5.0	5.0 5.0	ns
t _{su}	Minimum Setup Time, D to LE	$V_{CC} = 3.3 \pm 0.3 V$ $V_{CC} = 5.0 \pm 0.5 V$		4.0 4.0	4.0 4.0	ns
t _h	Minimum Hold Time, D to LE	$V_{CC} = 3.3 \pm 0.3 V$ $V_{CC} = 5.0 \pm 0.5 V$		1.0 1.0	1.0 1.0	ns

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC373DWR2	SOIC-20	1000 Tape & Reel
MC74VHC373DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74VHC373DTR2	TSSOP-20*	2500 Tape & Reel
MC74VHC373MEL	SOEIAJ-20	2000 Tape & Reel
MC74VHC373MELG	SOEIAJ-20 (Pb-Free)	2000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

SWITCHING WAVEFORMS



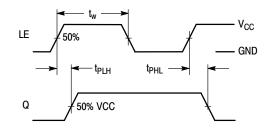


Figure 3.



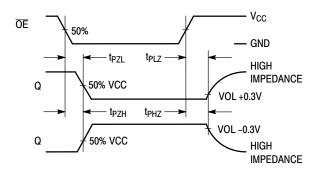


Figure 4.

V_{CC} 50% D GND t_{su} th -- V_{CC} LE 50% - GND

VALID



TEST CIRCUITS

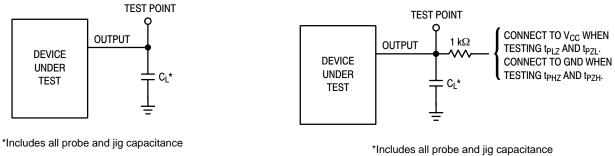


Figure 6.

Figure 7.

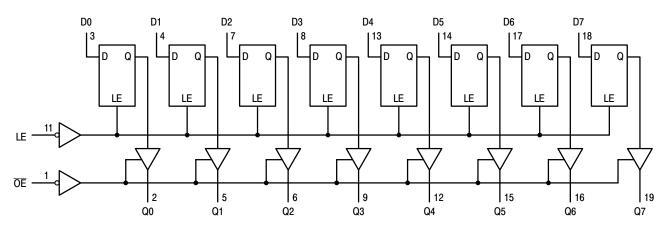


Figure 8. EXPANDED LOGIC DIAGRAM

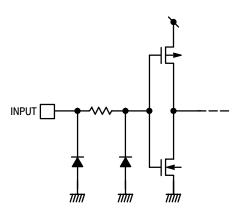
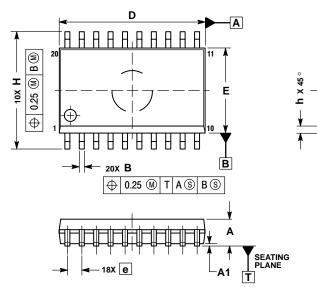


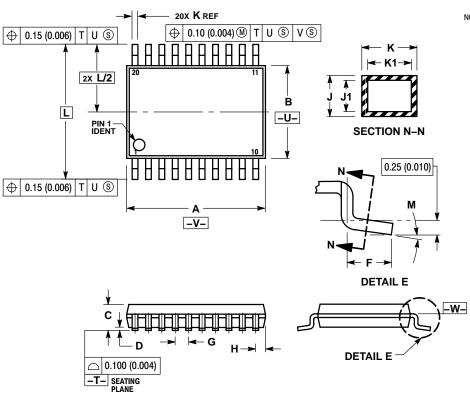
Figure 9. INPUT EQUIVALENT CIRCUIT

OUTLINE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



TSSOP-20 **DT SUFFIX** CASE 948E-02 ISSUE B



NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD
- 4
- 5 CONDITION.

	MILLIN	MILLIMETERS				
DIM	MIN	MAX				
Α	2.35	2.65				
A1	0.10	0.25				
В	0.35	0.49				
С	0.23	0.32				
D	12.65	12.95				
E	7.40	7.60				
е	1.27	BSC				
н	10.05	10.55				
h	0.25	0.75				
L	0.50	0.90				
θ	0 °	7 °				

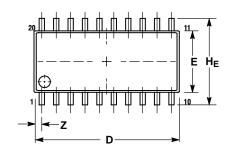
NOTES

- DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION PORCE NOT INCLUDE INTERLEAD.
- USUND PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 4.
- PEH SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0°	8°	0 °	8°	

OUTLINE DIMENSIONS

SOEIAJ-20 M SUFFIX CASE 967-01 ISSUE O



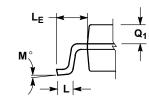
A₁

0.10 (0.004)

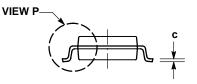
е

 \oplus

0.13 (0.005) 🕅



DETAIL P



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q1	0.70	0.90	0.028	0.035
Ζ		0.81		0.032

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use to all applicable to SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunit/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082–1312 USA Phone: 480–829–7710 or 800–344–3860 Toll Free USA/Canada Fax: 480–829–7709 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2–9–1 Kamimeguro, Meguro–ku, Tokyo, Japan 153–0051 Phone: 81–3–5773–3850 ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.